



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

SURFACE MOUNT

SCHOTTKY BARRIER DIODE

VOLTAGE 40 Volts CURRENT 0.1 Ampere

CH425DWGP

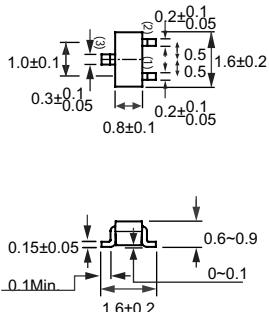
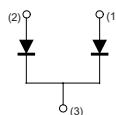
FEATURE

- * Small surface mounting type. (SC-75/SOT-416)
- * Low VF. (VF=0.45V Typ. at 100mA)
- * High reliability

CONSTRUCTION

- * Silicon epitaxial planar

CIRCUIT



Dimensions in millimeters

SC-75/SOT-416

MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	CH425DWGP	UNITS
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	40	Volts
Maximum RMS Voltage	V _{RMS}	28	Volts
Maximum DC Blocking Voltage	V _{DC}	40	Volts
Maximum Average Forward Rectified Current	I _o	0.1	Amps
Peak Forward Surge Current at 8.3 mSec single half sine-wave	I _{FSM}	1.0	Amps
Typical Junction Capacitance between Terminal (Note 1)	C _J	6.0	pF
Maximum Operating Temperature Range	T _J	+125	°C
Storage Temperature Range	T _{STG}	-40 to +125	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CH425DWGP	UNITS
Maximum Instantaneous Forward Voltage at I _{F(1)} = 50mA	V _{F(1)}	0.40	Volts
Maximum Instantaneous Forward Voltage at I _{F(2)} = 100mA	V _{F(2)}	0.55	Volts
Maximum Average Reverse Current at V _R = 10V	I _R	30	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 10.0 volts.
2. ESD sensitive product handling required.

2009-07

RATING CHARACTERISTIC CURVES (CH425DWGP)

FIG. 1 - FORWARD CHARACTERISTICS

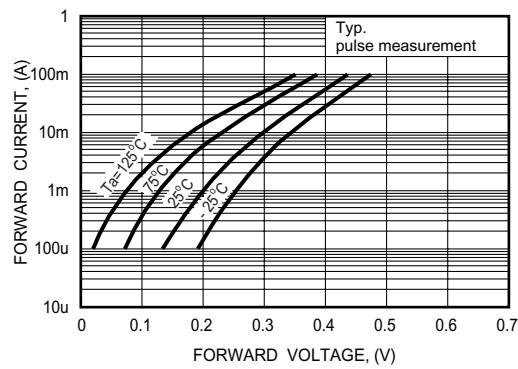


FIG. 2 - REVERSE CHARACTERISTICS

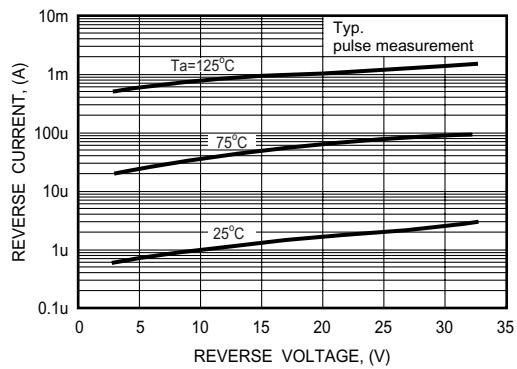


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

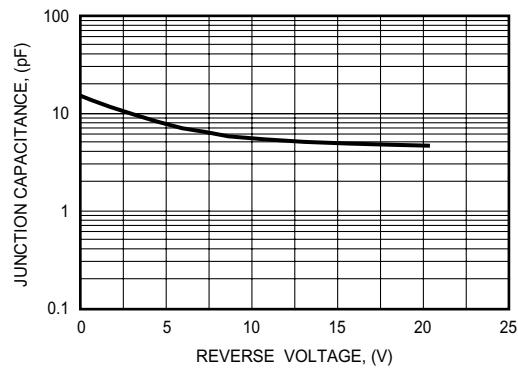


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

